

2SK2247

Silicon N Channel MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device - - - can be driven from 5 V source.
- Suitable for DC – DC converter, motor drive, power switch, solenoid drive

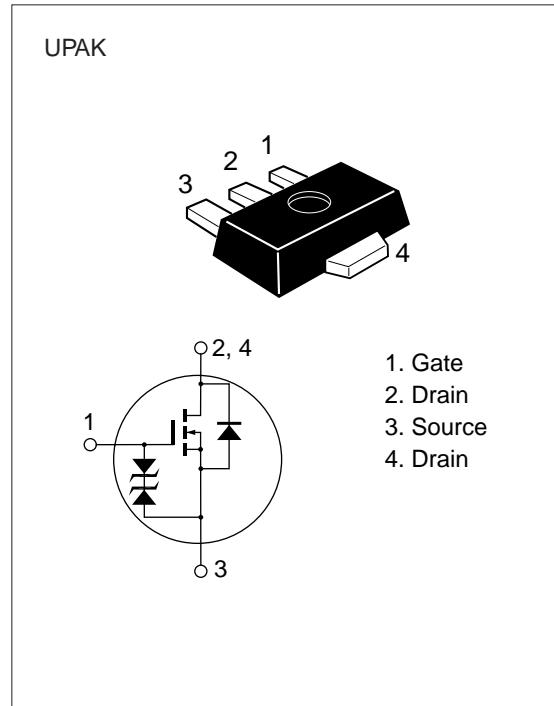


Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	2	A
Drain peak current	I _{D(pulse)} *	4	A
Body-drain diode reverse drain current	I _{DR}	2	A
Channel dissipation	P _{ch} **	1	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 100 µs, duty cycle ≤ 10 %

** When using the alumina ceramic board (12.5 × 20 × 0.7mm)

*** Marking is "QY"

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	30	—	—	V	I _D = 1 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR)GSS}	±20	—	—	V	I _G = ±10 µA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±5	µA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	1	µA	V _{DS} = 24 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	1.0	1.5	2.0	V	I _D = 100 µA, V _{DS} = 10 V
Static drain to source on state resistance	R _{DS(on)}	—	0.3	0.45	Ω	I _D = 1 A V _{GS} = 4 V *
		—	0.22	0.35	Ω	I _D = 1 A V _{GS} = 10 V *
Forward transfer admittance	y _{fs}	1.5	1.9	—	S	I _D = 1 A V _{DS} = 10 V *
Input capacitance	C _{iss}	—	177	—	pF	V _{DS} = 10 V
Output capacitance	C _{oss}	—	116	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	43	—	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	—	8	—	ns	I _D = 1 A
Rise time	t _r	—	14	—	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	—	37	—	ns	R _L = 30 Ω
Fall time	t _f	—	33	—	ns	PW = 2 µs

* Pulse Test

